4 Megabit ROM + 256 Kilobit SRAM ROM/RAM Combo

SST30VR043

Data Sheet

FEATURES:

- **Organized as 512K x8 ROM + 32K x8 SRAM**
- **ROM/RAM combo on a monolithic chip**
- **Wide Operating Voltage Range: 2.7-3.3V**
- **Chip Access Time**
  - 2.7V Operation: 500 ns (Max.)
- **Low Power Dissipation:**
  - Standby
    3.0V Operation: 1.0µW (Typical)
  - Operating
    3.0V Operation: 3.0 mW (Typical)
- **Fully Static Operation**
  - No clock or refresh required
- **Three state Outputs**
- **Packages Available**
  - 32-Pin TSOP (8mm x 20mm)
  - 32-Pin STSOP (8mm x13.4mm)

PRODUCT DESCRIPTION

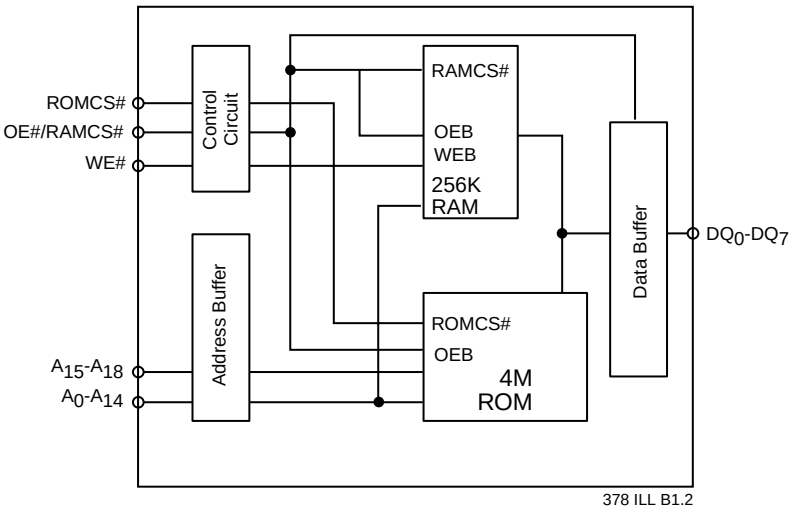
The SST30VR043 is a ROM/RAM combo chip consisting of 4 Mbit Read Only Memory organized as 512 KBytes and a 256 Kbit Static Random Access Memory organized as 32 KBytes. Output Enable Input (OE#) is pin-shared with RAMCS# (RAM Enable Input) signal in order to maintain the standard 32 pin TSOP package.

The device is fabricated using SST's advanced CMOS low power process technology.

The SST30VR043 has an output enable input for precise control of the data outputs. It also has two (2) separate chip enable inputs for selection of either RAM or ROM and minimize current drain during power-down mode.

The SST30VR043 is particularly well suited for use in low voltage (2.7-3.3V) operation such as pagers, organizers and other handheld applications.

FUNCTIONAL BLOCK DIAGRAM OF SST30VR043 ROM/RAM COMBO



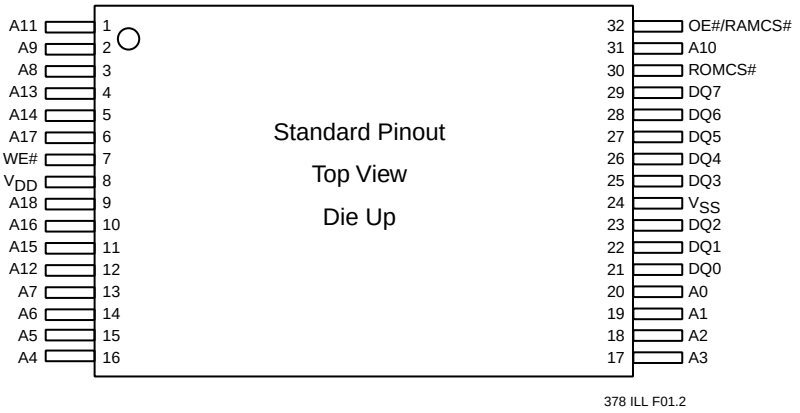


FIGURE 1: PIN ASSIGNMENTS

TABLE 1: PIN DESCRIPTION

Symbol	Pin Name
A_0-A_{18}	Address Inputs
WE#	Write Enable Input
OE#/RAMCS#	Output Enable/RAM Enable Input
ROMCS#	ROM Enable Input
DQ_0-DQ_7	Data Inputs/Outputs
V_{DD}	Power Supply
Vss	Ground

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Absolute Maximum Stress Ratings (Applied conditions greater than those listed under "Absolute Maximum Stress Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Voltage on Any Pin Relative to V_{SS} ..... -0.5V to V_{DD}+ 0.5V
Voltage on V_{DD} Supply Relative to V_{SS} ..... -0.5 to 4.0V
Power Dissipation 1.0W
Storage Temperature ..... -65°C to +150°C
Operating Temperature ..... -20°C to +70°C
Soldering Temperature (10 Seconds Lead Only) ..... 260°C

OPERATING RANGE

Range	Ambient Temp	V_{DD}
Commercial	0 °C to +70 °C	2.7-3.3V
Extended	-20 °C to +70 °C	2.7-3.3V
Industrial	-40 °C to +85 °C	2.7-3.3V

AC CONDITIONS OF TEST

Input Pulse Level 0-3V
Input & Output Timing Reference Levels 1.5V
Input Rise/Fall Time ..... 5 ns
Output Load ..... C_L = 100 pF

TABLE 2: RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Units
V_{DD}	Supply Voltage	2.7	3.3	V
V_{SS}	Ground	0	0	V
V_{IH}	Input High Voltage	2.4	V_{DD}+0.5	V
V_{IL}	Input Low Voltage	-0.3	0.3	V

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TABLE 3: DC OPERATING CHARACTERISTICS

		V_{DD} = 3.0±0.3V			
Symbol	Parameter	Min	Max	Units	Test Conditions
I_{LI}	Input Leakage Current	-1	1	µA	V_{IN} =V_{SS} to V_{DD}
I_{LO}	Output Leakage Current	-1	1	µA	ROMCS# = RAMCS# = V_{IH} or OE# = V_{IH} or WE# = V_{IL}, $V_{I/O}$ = V_{SS} to V_{DD}
I_{DD1}	ROM Operating Supply Current		4.0+1.1(f)	mA	ROMCS# = V_{IL}, RAMCS# = V_{IH}, V_{IN} = V_{IH} or V_{IL} $I_{I/O}$ = Opens
I_{DD2}	RAM Operating Supply Current		2.5+1(f)	mA	ROMCS# = V_{IH}, RAMCS# = V_{IL}, $I_{I/O}$ = Opens
I_{SB}	Standby V_{DD} Current		10	µA	ROMCS# ≥ V_{DD}-0.2V, RAMCS# ≥ V_{DD}-0.2V V_{IN} ≥ V_{DD}-0.2V or V_{IN} ≤ 0.2V
V_{OL}	Output Low Voltage		0.4	V	I_{OL} = 1.0 mA
V_{OH}	Output High Voltage	2.2		V	I_{OH} = -0.5 mA

Note: f = 1/cycle time (MHz)

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TABLE 4: CAPACITANCE (Ta = 25 °C, f=1 Mhz)

Parameter	Description	Test Condition	Maximum
$C_{I/O}$	I/O Capacitance	$V_{I/O}$ = 0V	8 pF
C_{IN}	Input Capacitance	V_{IN} = 0V	6 pF

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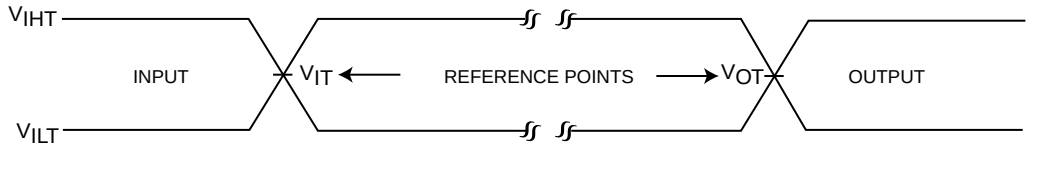

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AC test inputs are driven at V_{IHT} (0.9 V_{DD}) for a logic "1" and V_{ILT} (0.1 V_{DD}) for a logic "0". Measurement reference points for inputs and outputs are V_{IT} (0.5 V_{DD}) and V_{OT} (0.5 V_{DD}). Inputs rise and fall times (10% ↔ 90%) are <5 ns.

Note: V_{HT}–V_{HIGH} Test
V_{LT}–V_{LOW} Test
V_{IHT}–V_{INPUT} HIGH Test
V_{ILT}–V_{INPUT} LOW Test

FIGURE 2: AC INPUT/OUTPUT REFERENCE WAVEFORMS

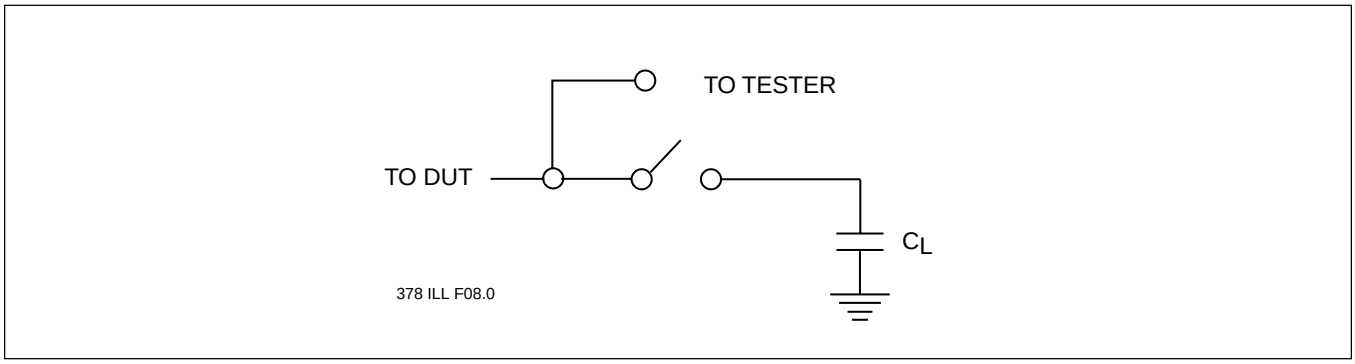

FIGURE 3: A TEST LOAD EXAMPLE

AC CHARACTERISTICS

I. ROM Operation

TABLE 5: READ CYCLE TIMING PARAMETERS

Symbol	Parameter	V_{DD}=3.0 V ± 0.3 Min	V_{DD}=3.0 V ± 0.3 Max	Unit
T_{RC}	Read Cycle Time	500		ns
T_{AA}	Address Access Time		500	ns
T_{CO}	Chip Select to Output		500	ns
T_{OE}	Output Enable to Valid Output		250	ns
T_{LZ}	Chip Select to Low-Z Output	10		ns
T_{OLZ}	Output Enable to Low-Z Output	10		ns
T_{HZ}	Chip Disable to High-Z Output		40	ns
T_{OHZ}	Output Disable to High-Z Output		40	ns
T_{OH}	Output Hold from Address Change	15		ns

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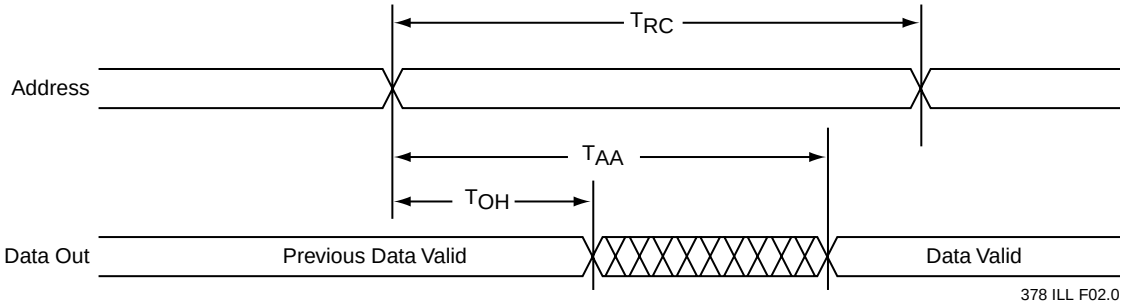
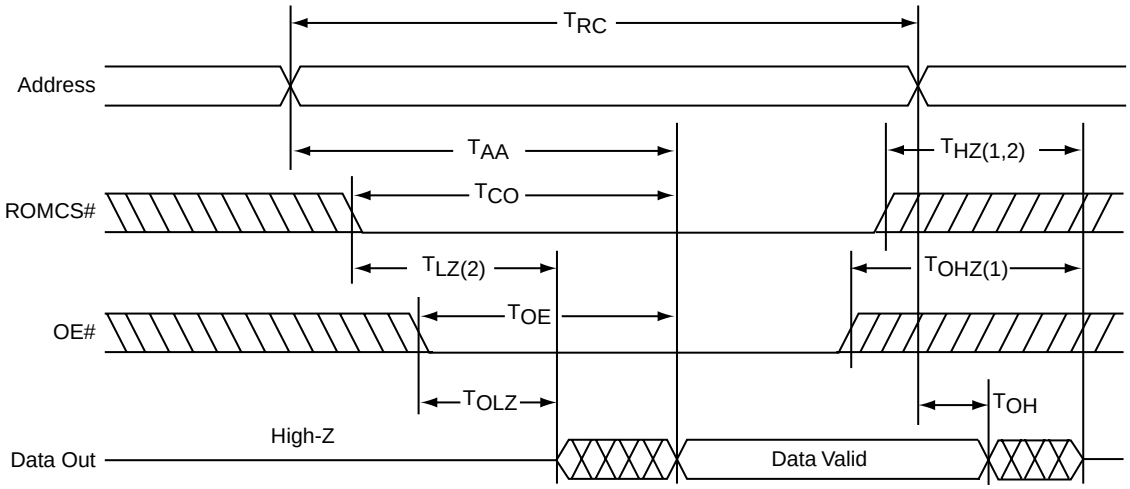


FIGURE 4: ROM READ CYCLE TIMING DIAGRAM (ADDRESS CONTROLLED) (ROMCS# = OE# = V_{IL})



Notes: 1. T_{HZ} and T_{OHZ} are defined as the time at which the outputs achieve the open circuit condition and are referenced to the V_{OH} or V_{OL}.
2. At any given temperature and voltage condition T_{HZ}(max) is less than T_{LZ}(min) both for a given device and from device to device.

FIGURE 5: ROM READ CYCLE TIMING DIAGRAM (ROMCS# & OE# CONTROLLED)

II. SRAM Operation (ROMCS# = V_{IH})

TABLE 6: READ CYCLE TIMING PARAMETERS

Symbol	Parameter	V_{DD}=3.0 V ± 0.3 Min	Max	Unit
T_{RC}	Read Cycle Time	500		ns
T_{AA}	Address Access Time		500	ns
T_{CO}	Chip Select to Output		500	ns
T_{LZ}	Chip Select to Low-Z Output	10		ns
T_{HZ}	Chip Disable to High-Z Output		40	ns
T_{OH}	Output Hold from Address Change	15		ns

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TABLE 7: WRITE CYCLE TIMING PARAMETERS

Symbol	Parameter	V_{DD}=3.0 V ± 0.3 Min	Max	Unit
T_{WC}	Write Cycle Time	500		ns
T_{CW}	Chip Select to End-of-Write	365		ns
T_{AW}	Address Valid to End-of-Write	400		ns
T_{AS}	Address Set-up Time	0		ns
T_{WP}	Write Pulse Width	400		ns
T_{WR}	Write Recovery Time	0		ns
T_{WHZ}	Write to Output High-Z		80	ns
T_{DW}	Data to Write Time Overlap	200		ns
T_{DH}	Data Hold from Write Time	0		ns
T_{OW}	End Write to Output Low-Z	10		ns

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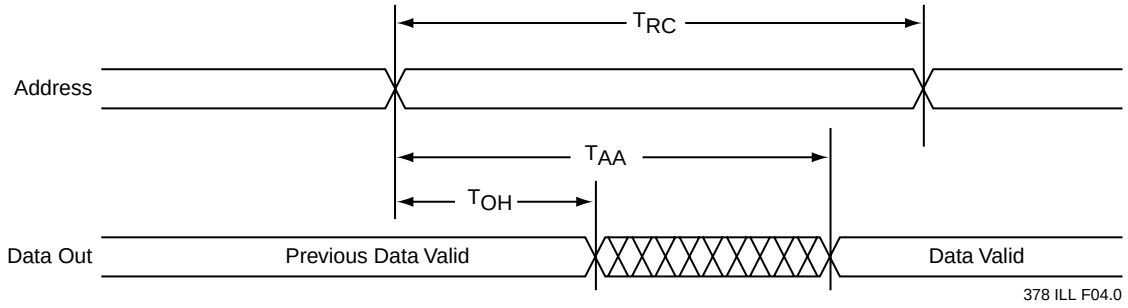
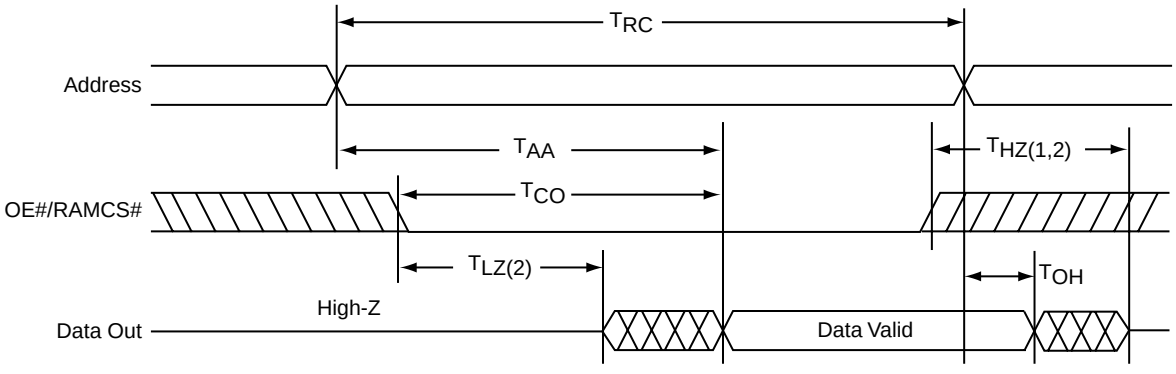
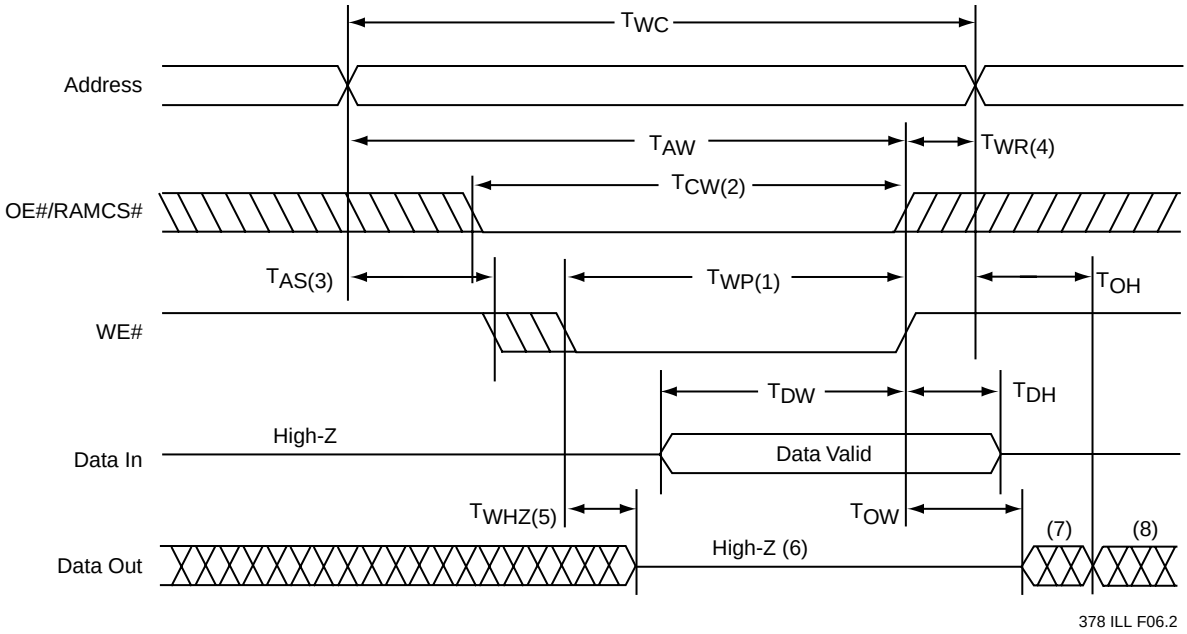


FIGURE 6: SRAM READ CYCLE TIMING DIAGRAM (ADDRESS CONTROLLED) ($OE\#/RAMCS\# = V_{IL}$, $WE\# = V_{IH}$)



Notes:
1. T_{HZ} and T_{OHZ} are defined as the time at which the outputs achieve the open circuit condition and are referenced to the V_{OH} or V_{OL}.
2. At any given temperature and voltage condition T_{HZ}(max) is less than T_{LZ}(min) both for a given device and from device to device.
3. WE# is high for Read cycle.

FIGURE 7: SRAM READ CYCLE TIMING DIAGRAM (OE#/RAMCS# CONTROLLED)



Notes:
1. A write occurs during the overlap (T_{WP}) of a low RAMCS# and low WE#. A write begins at the latest transition among RAMCS# going low and WE# going low: A write end at the earliest transition among RAMCS# going high and WE# going high, T_{WP} is measured from the beginning of write to the end of write.
2. T_{CW} is measured from the later of RAMCS# going low to the end of write.
3. T_{AS} is measured from the address valid to the beginning of write.
4. T_{WR} is measured from the end of write to the address change.
5. If RAMCS#, WE# are in the read mode during this period, the I/O pins are in the outputs Low-Z state. Inputs of opposite phase of the output must not be applied because bus contention can occur.
6. If RAMCS# goes low simultaneously with WE# going low or after WE# going low, the outputs remain high impedance state.
7. D_{OUT} is the same phase of the latest written data in this write cycle.
8. D_{OUT} is the read data of new address
9. ROMCS# = V_{IH}

FIGURE 8: SRAM WRITE CYCLE TIMING DIAGRAM

TABLE 8: FUNCTIONAL DESCRIPTION/TRUTH TABLE

A0=A18	ROMCS#	OE#/RAMCS# (PIN 32)	WE#	DQ_0-DQ_7	
X	H	H	X	Z	Standby
A0-A18	L	OE# (H)	X	Z	Output Floating
A0-A18	L	OE# (L)	X	Dout	ROM Read
Only A0-A14 are valid *	H	RAMCS# (L)	H	Dout	RAM Read
Only A0-A14 are valid *	H	RAMCS# (L)	L	Din	RAM Write

* A15-A18 must be fixed to “L” or “H”

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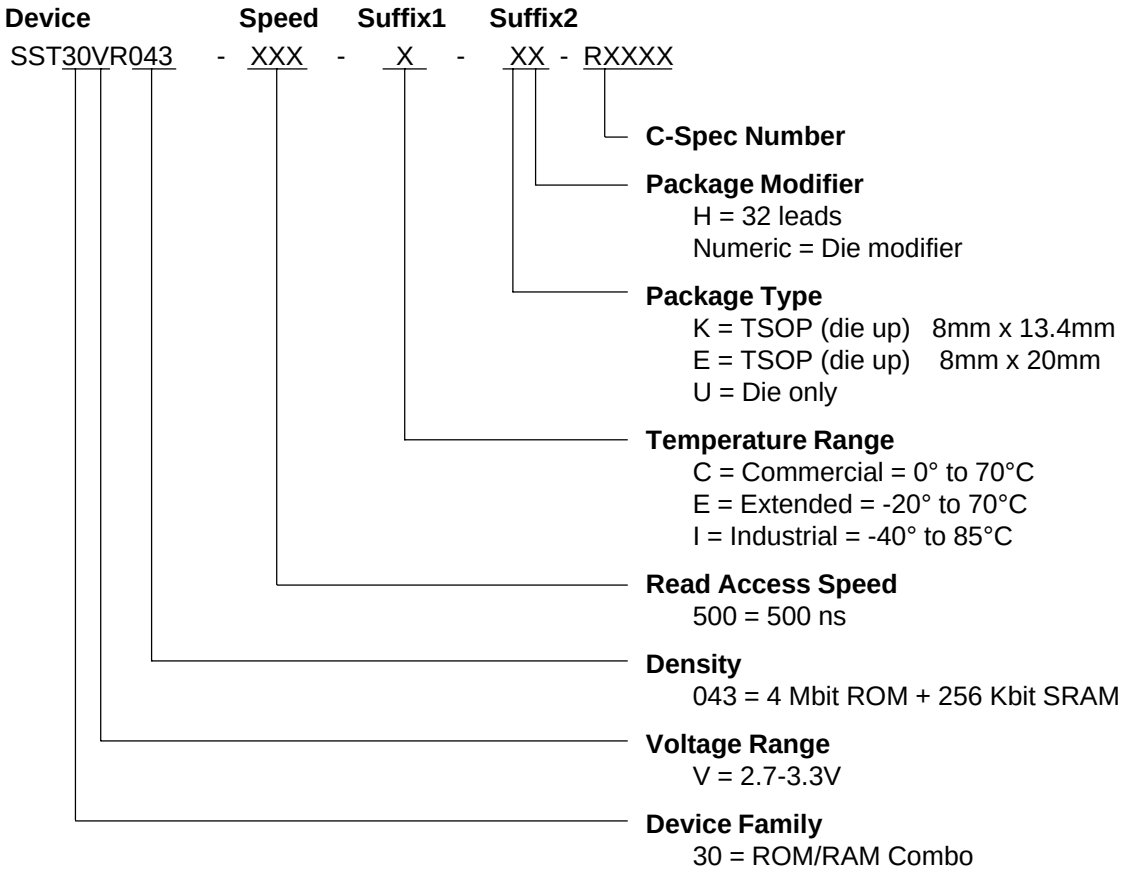
Note: (1) OE# & RAMCS# are pin-shared
(2) X means Don’t Care.

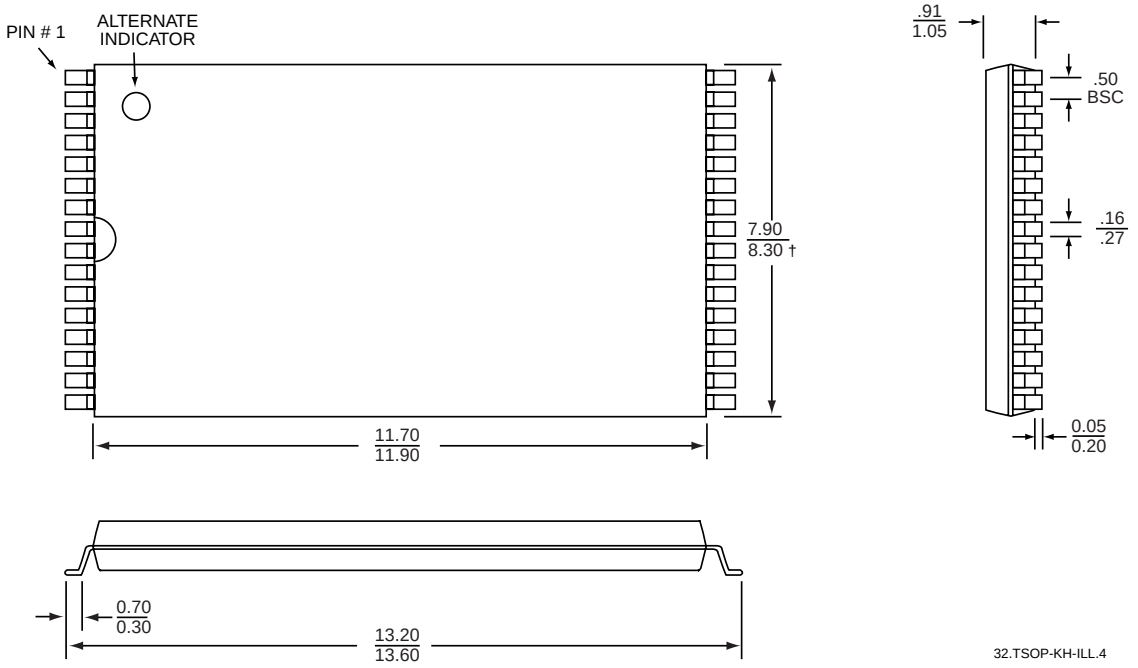


SST30VR043 Valid combinations

SST30VR043-500-C-KH	SST30VR043-500-C-EH	SST30VR043-500-C-U1
SST30VR043-500-E-KH	SST30VR043-500-E-EH	
SST30VR043-500-I-KH	SST30VR043-500-I-EH	

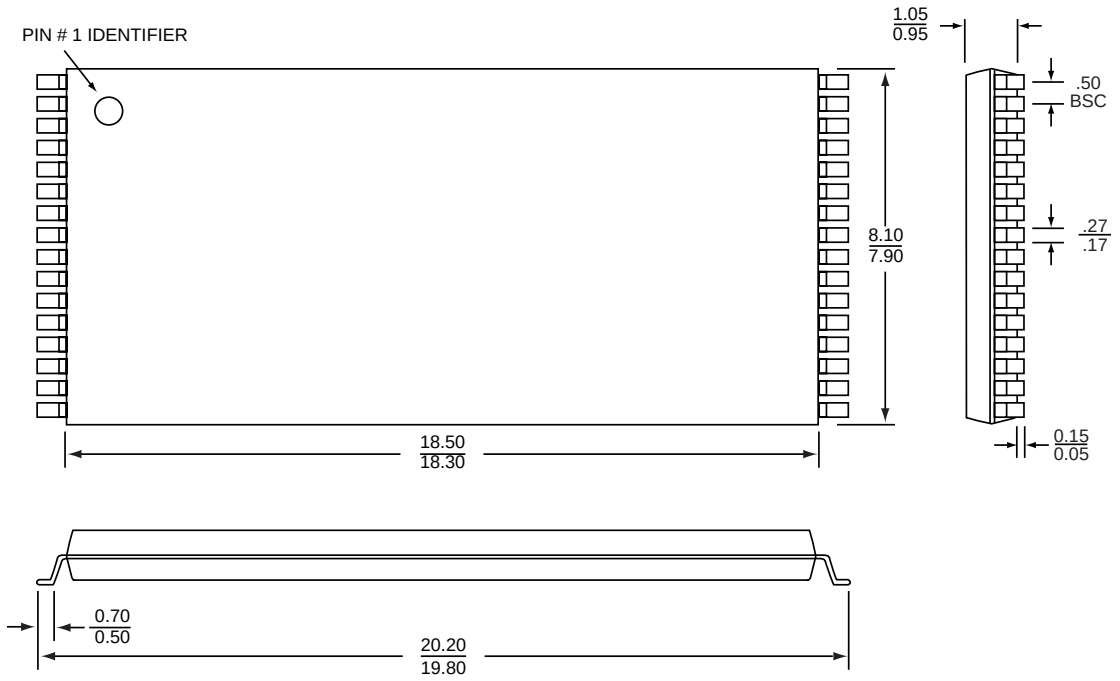
Example: Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.

PACKAGING DIAGRAMS



Note: 1. Complies with JEDEC publication 95 MO-142 BA dimensions (except as noted), although some dimensions may be more stringent.
† = JEDEC max is 8.1; SST max is *less* stringent
2. All linear dimensions are in millimeters (min/max).
3. Coplanarity: 0.1 (±.05) mm.

32-PIN THIN SMALL OUTLINE PACKAGE (TSOP) 8MM X 13.4MM
SST PACKAGE CODE: KH



Note: 1. Complies with JEDEC publication 95 MO-142 BD dimensions, although some dimensions may be more stringent.
2. All linear dimensions are in millimeters (min/max).
3. Coplanarity: 0.1 (±.05) mm.

32.TSOP-EH-ILL.3

32-PIN THIN SMALL OUTLINE PACKAGE (TSOP) 8MM X 20MM
SST PACKAGE CODE: EH